Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V _{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	-	330	mA	
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	240	mA	
Static characteristics (per transistor)								
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 200 mA; T_j = 25 °C		-	2.2	2.8	Ω	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	654	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 $G2$ $G2$
4	S2	source TR2	☐1 ☐2 ☐3 ———— (2.2—22)	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX7002BKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
NX7002BKS	LT%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor	,	_			_
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	330	mA
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	240	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	150	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	0.8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	285	mW
			[1]	-	320	mW
		T _{sp} = 25 °C		-	870	mW
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	200	mA
Per device				'	-	
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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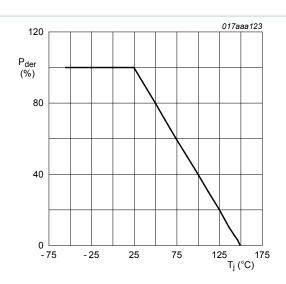


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

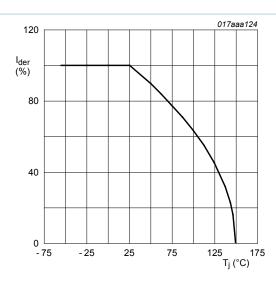
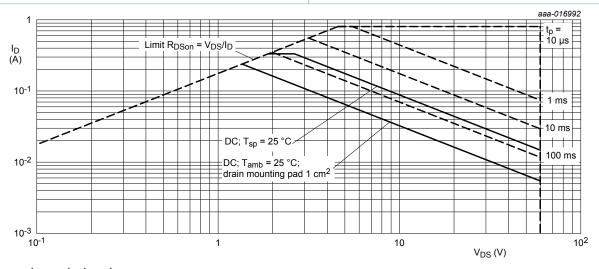


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



 I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

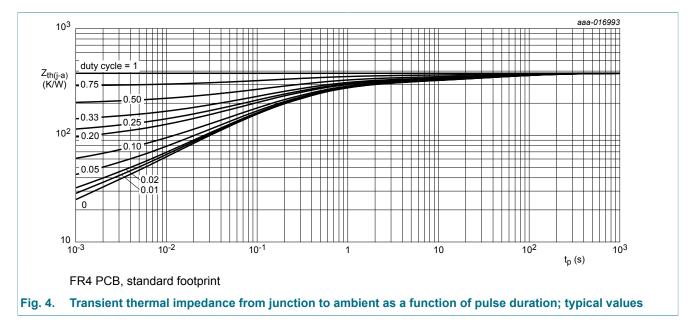
60 V, dual N-channel Trench MOSFET

9. Thermal characteristics

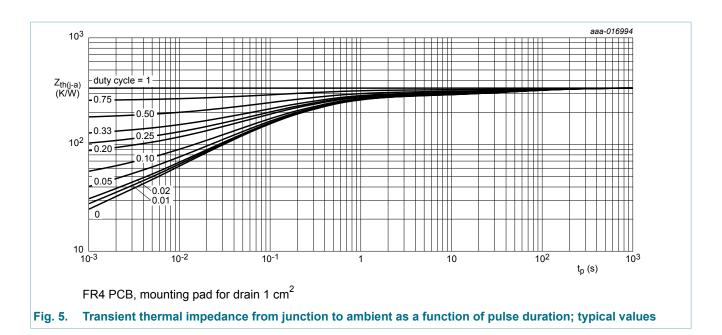
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
from ju	thermal resistance	-	[1]	-	380	440	K/W	
	from junction to ambient		[2]	-	340	390	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	125	145	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics (per transistor)			'		
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.3	μA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.3	μΑ
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C	-	2.2	2.8	Ω
		V _{GS} = 10 V; I _D = 200 mA; T _j = 150 °C	-	4.5	5.7	Ω
		V_{GS} = 5 V; I_{D} = 200 mA; T_{j} = 25 °C	-	2.5	3.2	Ω
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	600	-	mS
R _G	gate resistance	f = 1 MHz	-	2.5	-	Ω
Dynamic c	haracteristics (per transist	or)	1		'	
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 200 \text{ mA}; V_{GS} = 10 \text{ V};$	-	1	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	23.6	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.6	-	pF
C _{rss}	reverse transfer capacitance		-	3	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; I_{D} = 200 mA; V_{GS} = 10 V;	-	4.7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4.3	-	ns
t _{d(off)}	turn-off delay time		-	6.9	-	ns
t _f	fall time		-	2.9	-	ns
Source-dra	ain diode (per transistor)		1	1	1	
V _{SD}	source-drain voltage	$I_S = 50 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.87	1.2	V

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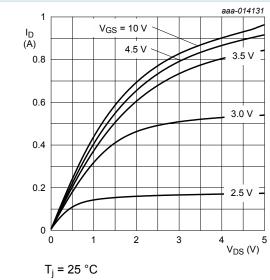
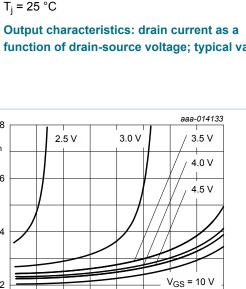


Fig. 6. function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}C$

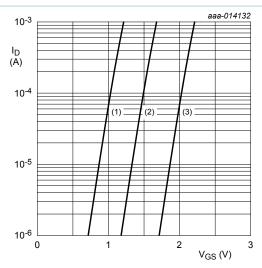
8

R_{DSon} (Ω)

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

0.4

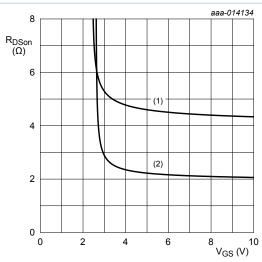
0.8



 $T_i = 25 \,^{\circ}C; \, V_{DS} = 5 \,^{\circ}V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 0.2 A$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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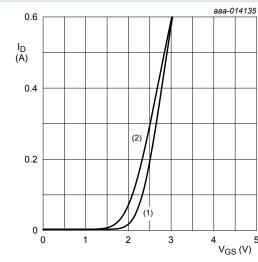
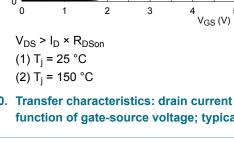
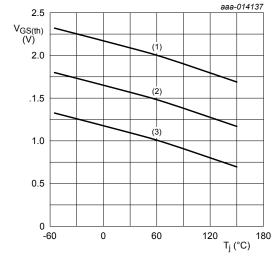


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values





 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

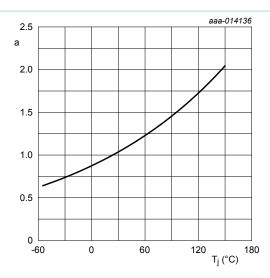
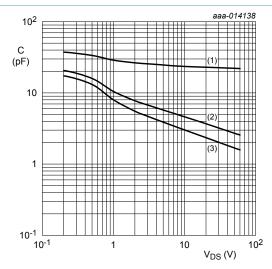


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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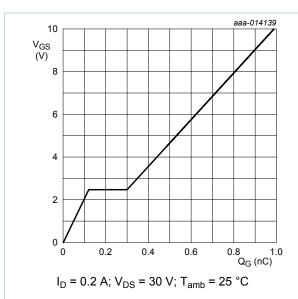


Fig. 14. Gate-source voltage as a function of gate charge; typical values

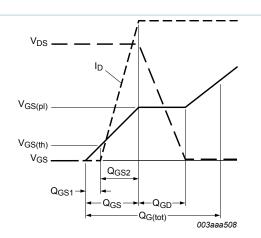
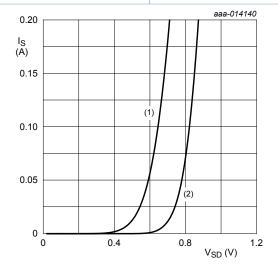


Fig. 15. MOSFET transistor: Gate charge waveform definitions

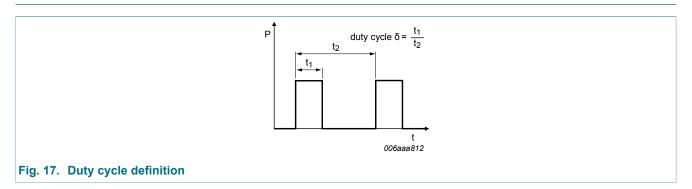


 $V_{GS} = 0 V$ (1) $T_j = 150 °C$ (2) $T_i = 25 °C$

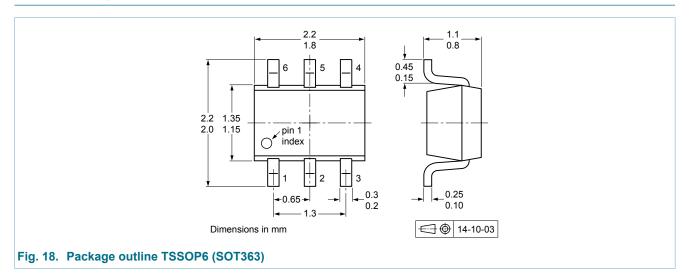
Fig. 16. Source current as a function of source-drain voltage; typical values

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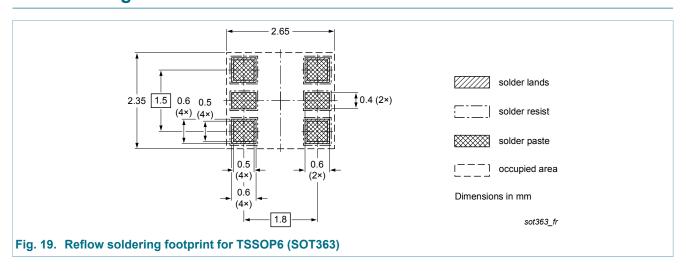
11. Test information



12. Package outline



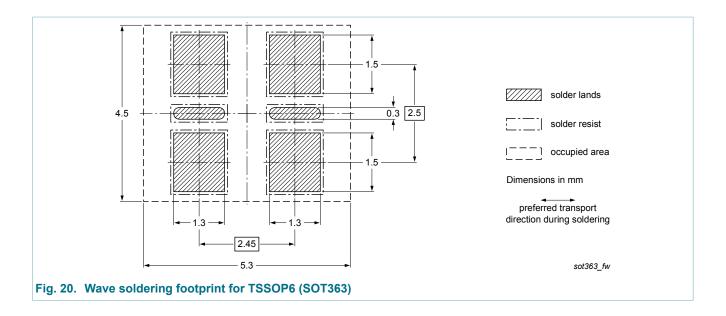
13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002BKS v.1	20150512	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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